

2N3235
N-P-N SILICON TRANSISTOR

ABSOLUTE MAXIMUM RATINGS

VCEX	VCER	VCEO	VEBO	IC	IB	Pc	T storage	TJ
V	V	V	V	A	A	W	°C	°C
90	65	55	7	15	7	117	-65 to +200	-65 to +200

ELECTRICAL CHARACTERISTICS: $T_J = 25^\circ\text{C}$ unless otherwise specified.

Characteristic	Symbol	Min.	Max.	Unit
DC Current Gain*				
IC = 4 A, VCE = 4 V	hFE	20	70	—
Collector-to-Emitter Voltage*				
IC = 100 mA	VCEO	55	—	V
Collector-to-Emitter Saturation Voltage*				
IC = 4 A, IB = 400 mA	VCE(s)	—	1.1	V
Base-to-Emitter Saturation Voltage*				
IC = 4 A, IB = 400 mA	VBE(s)	—	1.8	V
Collector Cutoff Current				
VCEX = 90 V, VBE = -1.5 V	ICEX	—	5	mA
VCER = 65 V, RBE = 100 ohms	ICER	—	5	mA
Emitter Cutoff Current				
VEBO = 7 V	IEBO	—	5	mA
Thermal Resistance				
Junction-to-Case	θ_{J-C}	—	1.5	°C/W

Lead temperature $\leq 235^\circ\text{C}$ for 10 seconds 1/32 inch from case.

*Pulse width $\leq 300 \mu\text{sec}$, duty cycle $\leq 2\%$.

